



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

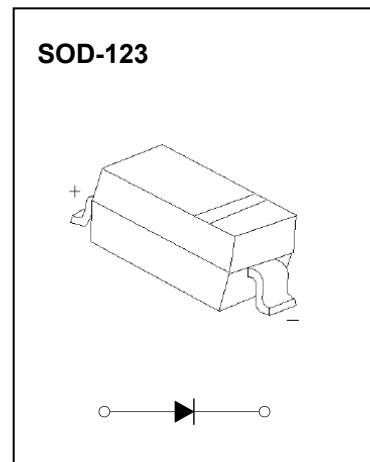
## SOD-123 Plastic-Encapsulate Diodes

### BAT42W/BAT43W SCHOTTKY BARRIER DIODE

#### FEATURES

- Low Forward Voltage Drop
- Fast Switching Time
- Surface Mount Package Ideally Suited for Automatic Insertion

MARKING: BAT42W S7  
BAT43W S8



#### Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25°C

Parameter	Symbol	BAT42W/BAT43W		Unit
Peak Repetitive Peak Reverse Voltage	V <sub>RRM</sub>			
Working Peak Reverse Voltage	V <sub>RWM</sub>	30		V
DC Blocking Voltage	V <sub>R</sub>			
RMS Reverse Voltage	V <sub>R(RMS)</sub>	21		V
Forward Continuous Current	I <sub>FM</sub>	200		mA
Repetitive Peak Forward Current @t<1.0s	I <sub>FRM</sub>	500		mA
Peak Forward Surge Current @t<10ms	I <sub>FSM</sub>	4.0		A
Power Dissipation	P <sub>D</sub>	500		mW
Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	200		°C/W
Junction temperature	T <sub>J</sub>	125		°C
Storage Temperature	T <sub>STG</sub>	-55~+150		°C

#### Electrical Ratings @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V <sub>(BR)</sub>	30			V	IR=10µA
Forward voltage	V <sub>F</sub>			1.0	V	I <sub>F</sub> =200mA
	V <sub>F</sub>			0.4	V	I <sub>F</sub> =10mA
	V <sub>F</sub>			0.65	V	I <sub>F</sub> =50mA
	V <sub>F</sub>	0.26		0.33	V	I <sub>F</sub> =2mA
	V <sub>F</sub>			0.45	V	I <sub>F</sub> =15mA
Reverse current	I <sub>R</sub>			0.5	µA	V <sub>R</sub> =25V
Capacitance between terminals	C <sub>T</sub>			10	pF	V <sub>R</sub> =1.0V,f=1.0MHz
Reverse recovery time	t <sub>rr</sub>			5	ns	I <sub>F</sub> =I <sub>R</sub> =10mA I <sub>rr</sub> =0.1XI <sub>R</sub> ,R <sub>L</sub> =100Ω

# Typical Characteristics

BAT43W

